

## IPI80N06S4L05AKSA2

#### IPI80N06S4L05AKSA2 Information



For Reference Only

Part Number IPI80N06S4L05AKSA2
Manufacturer Infineon Technologies

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH TO262-3

Package TO-262-3 Long Leads, I2Pak, TO-262AA

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



Request a Quote

# **Certified Quality**

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









## IPI80N06S4L05AKSA2 Specifications

Manufacturer Part Number         IPI80N06S4L05AKSA2           Manufacturer         Infineon Technologies           Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-262-3 Long Leads, I2Pak, TO-262AA           Series         Automotive, AEC-Q101, OptiMOS?           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         60V           Current - Continuous Drain (Id) @ 25°C         80A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         4.5V, 10V           Vgs(th) (Max) @ Id         2.2V @ 60μA           Gate Charge (Qg) (Max) @ Vgs         110nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         8180pF @ 25V           Vgs (Max)         ±16V           FET Feature         -           Power Dissipation (Max)         107W (Tc)           Rds On (Max) @ Id, Vgs         8.5 mOhm @ 40A, 4.5V           Operating Temperature         -55°C ~ 175°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         PG-TO262-3-1           Package / Case         TO-262-3 Long Leads, 12Pak, TO-262AA		
Category  Discrete Semiconductor Products  Transistors - FETs, MOSFETs - Single  Package  TO-262-3 Long Leads, 12Pak, TO-262AA  Series  Automotive, AEC-Q101, OptiMOS?  FET Type  N-Channel  Technology  MOSFET (Metal Oxide)  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  80A (Tc)  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  110nC @ 10V  Input Capacitance (Ciss) (Max) @ Vds  8180pF @ 25V  Vgs (Max)  ±16V  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  107W (Tc)  Rds On (Max) @ Id, Vgs  Negrating Temperature  -55°C ~ 175°C (TJ)  Mounting Type  Supplier Device Package  PG-TO262-3-1  Package / Case  TO-262-3 Long Leads, 12Pak, TO-262AA	Manufacturer Part Number	IPI80N06S4L05AKSA2
Package         TO-262-3 Long Leads, 12Pak, TO-262AA           Series         Automotive, AEC-Q101, OptiMOS?           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         60V           Current - Continuous Drain (Id) @ 25°C         80A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         4.5V, 10V           Vgs(th) (Max) @ Id         2.2V @ 60μA           Gate Charge (Qg) (Max) @ Vgs         110nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         8180pF @ 25V           Vgs (Max)         ±16V           FET Feature         -           Power Dissipation (Max)         107W (Tc)           Rds On (Max) @ Id, Vgs         8.5 mOhm @ 40A, 4.5V           Operating Temperature         -55°C ~ 175°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         PG-TO262-3-1           Package / Case         TO-262-3 Long Leads, I2Pak, TO-262AA	Manufacturer	Infineon Technologies
PackageTO-262-3 Long Leads, 12Pak, TO-262AASeriesAutomotive, AEC-Q101, OptiMOS?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C80A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2.2V @ 60μAGate Charge (Qg) (Max) @ Vgs110nC @ 10VInput Capacitance (Ciss) (Max) @ Vds8180pF @ 25VVgs (Max)±16VFET Feature-Power Dissipation (Max)107W (Tc)Rds On (Max) @ Id, Vgs8.5 mOhm @ 40A, 4.5VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO262-3-1Package / CaseTO-262-3 Long Leads, 12Pak, TO-262AA	Category	Discrete Semiconductor Products
SeriesAutomotive, AEC-Q101, OptiMOS?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C80A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2.2V @ 60μAGate Charge (Qg) (Max) @ Vgs110nC @ 10VInput Capacitance (Ciss) (Max) @ Vds8180pF @ 25VVgs (Max)±16VFET Feature-Power Dissipation (Max)107W (Tc)Rds On (Max) @ Id, Vgs8.5 mOhm @ 40A, 4.5VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO262-3-1Package / CaseTO-262-3 Long Leads, 12Pak, TO-262AA		Transistors - FETs, MOSFETs - Single
FET Type  N-Channel  Technology  MOSFET (Metal Oxide)  Drain to Source Voltage (Vdss)  60V  Current - Continuous Drain (Id) @ 25°C  80A (Tc)  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Cate Charge (Qg) (Max) @ Vgs  110nC @ 10V  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  ±16V  FET Feature  - Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  107W (Tc)  Rds On (Max) @ Id, Vgs  Ns. mOhm @ 40A, 4.5V  Operating Temperature  -55°C ~ 175°C (TJ)  Mounting Type  Supplier Device Package  PG-TO262-3-1  Package / Case  NOA (Tc)  80A (Tc)  80	Package	TO-262-3 Long Leads, I2Pak, TO-262AA
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C80A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2.2V @ 60μAGate Charge (Qg) (Max) @ Vgs110nC @ 10VInput Capacitance (Ciss) (Max) @ Vds8180pF @ 25VVgs (Max)±16VFET Feature-Power Dissipation (Max)107W (Tc)Rds On (Max) @ Id, Vgs8.5 mOhm @ 40A, 4.5VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO262-3-1Package / CaseTO-262-3 Long Leads, 12Pak, TO-262AA	Series	Automotive, AEC-Q101, OptiMOS?
Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C80A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2.2V @ 60μAGate Charge (Qg) (Max) @ Vgs110nC @ 10VInput Capacitance (Ciss) (Max) @ Vds8180pF @ 25VVgs (Max)±16VFET Feature-Power Dissipation (Max)107W (Tc)Rds On (Max) @ Id, Vgs8.5 mOhm @ 40A, 4.5VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO262-3-1Package / CaseTO-262-3 Long Leads, I2Pak, TO-262AA	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Cate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  For Through Hole  Supplier Device Package  Package / Case  80A (Tc)  81B0F	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2.2V @ 60μAGate Charge (Qg) (Max) @ Vgs110nC @ 10VInput Capacitance (Ciss) (Max) @ Vds8180pF @ 25VVgs (Max)±16VFET Feature-Power Dissipation (Max)107W (Tc)Rds On (Max) @ Id, Vgs8.5 mOhm @ 40A, 4.5VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO262-3-1Package / CaseTO-262-3 Long Leads, I2Pak, TO-262AA	Drain to Source Voltage (Vdss)	60V
Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  Founding Type  Through Hole  Supplier Device Package  Package / Case  110nC @ 10V  8180pF @ 25V  107W (Tc)  107W (	Current - Continuous Drain (Id) @ 25°C	80A (Tc)
Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  8180pF @ 25V  Vgs (Max)  ±16V  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  0perating Temperature  -55°C ~ 175°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  PG-TO262-3-1  Package / Case  110nC @ 10V  8180pF @ 25V  8180pF @ 25V  **End **Common Common C	Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
Input Capacitance (Ciss) (Max) @ Vds  8180pF @ 25V  Vgs (Max)  #16V  FET Feature  - Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  8.5 mOhm @ 40A, 4.5V  Operating Temperature  -55°C ~ 175°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  PG-TO262-3-1  Package / Case  TO-262-3 Long Leads, 12Pak, TO-262AA	Vgs(th) (Max) @ Id	2.2V @ 60μA
Vgs (Max) ±16V  FET Feature -  Power Dissipation (Max) 107W (Tc)  Rds On (Max) @ Id, Vgs 8.5 mOhm @ 40A, 4.5V  Operating Temperature -55°C ~ 175°C (TJ)  Mounting Type Through Hole  Supplier Device Package PG-TO262-3-1  Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Gate Charge (Qg) (Max) @ Vgs	110nC @ 10V
FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  8.5 mOhm @ 40A, 4.5V  Operating Temperature  -55°C ~ 175°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  PG-TO262-3-1  Package / Case  TO-262-3 Long Leads, I2Pak, TO-262AA	Input Capacitance (Ciss) (Max) @ Vds	8180pF @ 25V
Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  8.5 mOhm @ 40A, 4.5V  Operating Temperature  -55°C ~ 175°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  PG-TO262-3-1  Package / Case  TO-262-3 Long Leads, I2Pak, TO-262AA	Vgs (Max)	±16V
Rds On (Max) @ Id, Vgs  8.5 mOhm @ 40A, 4.5V  Operating Temperature  -55°C ~ 175°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  PG-TO262-3-1  Package / Case  TO-262-3 Long Leads, I2Pak, TO-262AA	FET Feature	-
Operating Temperature  -55°C ~ 175°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  PG-TO262-3-1  Package / Case  TO-262-3 Long Leads, I2Pak, TO-262AA	Power Dissipation (Max)	107W (Tc)
Mounting Type Through Hole Supplier Device Package PG-TO262-3-1 Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Rds On (Max) @ Id, Vgs	8.5 mOhm @ 40A, 4.5V
Supplier Device Package PG-TO262-3-1 Package / Case PG-TO262-3-1 TO-262-3 Long Leads, I2Pak, TO-262AA	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Mounting Type	Through Hole
	Supplier Device Package	PG-TO262-3-1
Report errors?	Package / Case	TO-262-3 Long Leads, I2Pak, TO-262AA
		Report errors?

#### IPI80N06S4L05AKSA2 Guarantees



#### **Ouality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

### IPI80N06S4L05AKSA2 Payment Methods





















## IPI80N06S4L05AKSA2 Shipping Methods













If you have any question about IPI80N06S4L05AKSA2, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com